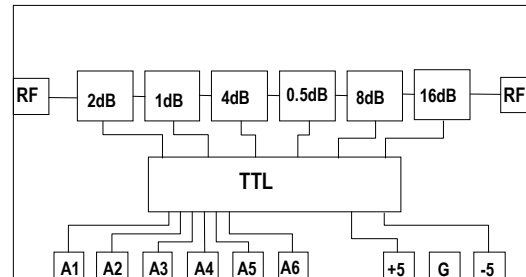


14.5-18.5 GHz 6-Bit Digital Attenuator

Features

- ◆ Frequency Range : 14.5 to 18.5 GHz
- ◆ 31.5dB Attenuation Range
- ◆ 3.25 dB Insertion loss max.
- ◆ 1.4 :1 Input/Output VSWR
- ◆ < 0.8 dB RMS Error
- ◆ TTL Control Inputs
- ◆ 0.5µm InGaAs pHEMT Technology
- ◆ Chip Size : 2.4 mm x 1.7 mm x 0.1 mm

Functional Diagram



Typical Applications

- ◆ Radar
- ◆ Military & Space
- ◆ Instrumentation
- ◆ Test and Measurements
- ◆ Instrumentation Applications

Description

The AMT2351031 is a 6-bit digital attenuator MMIC offering an attenuation range of 31.5dB in steps of 0.5dB. The attenuator bit values are 0.5dB (LSB), 1,2,4,8 and 16dB (MSB) for a total attenuation of 31.5dB. The attenuator features an excellent attenuation accuracy of 2.5dB over all 64 states. The attenuator provides an integral TTL driver, facilitating a 6-bit control. The driver operates on +5/-5V voltages with minimal DC power consumption. The MMIC die is fabricated using a robust 0.5µm InGaAs pHEMT technology.

Absolute Maximum Ratings ⁽¹⁾

Parameter	Absolute Maximum	Units
RF Input Power	25	dBm
Positive Supply Voltage	+6	V
Negative Supply Voltage	-6	V
Control Voltage	-0.5 to +5.5	V
Operating Temperature	-55 to +85	°C
Storage Temperature	-65 to +150	°C

1. Operation beyond these limits may cause permanent damage to the component

Electrical Specifications ⁽¹⁾ @ T_A = 25 °C, Z_o =50 Ω

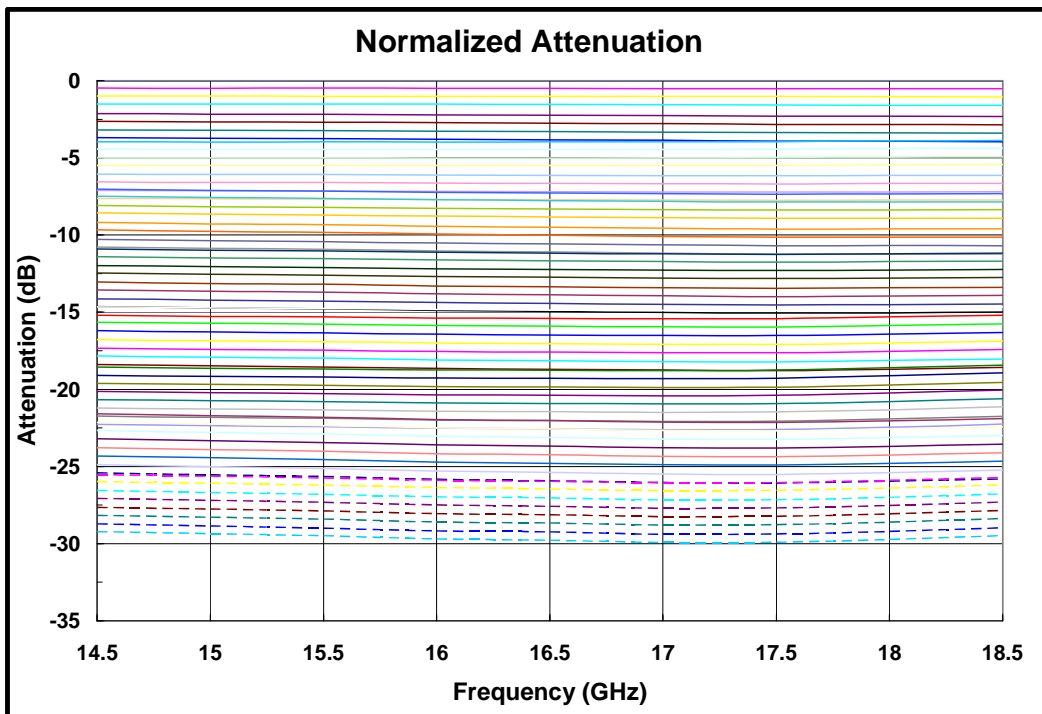
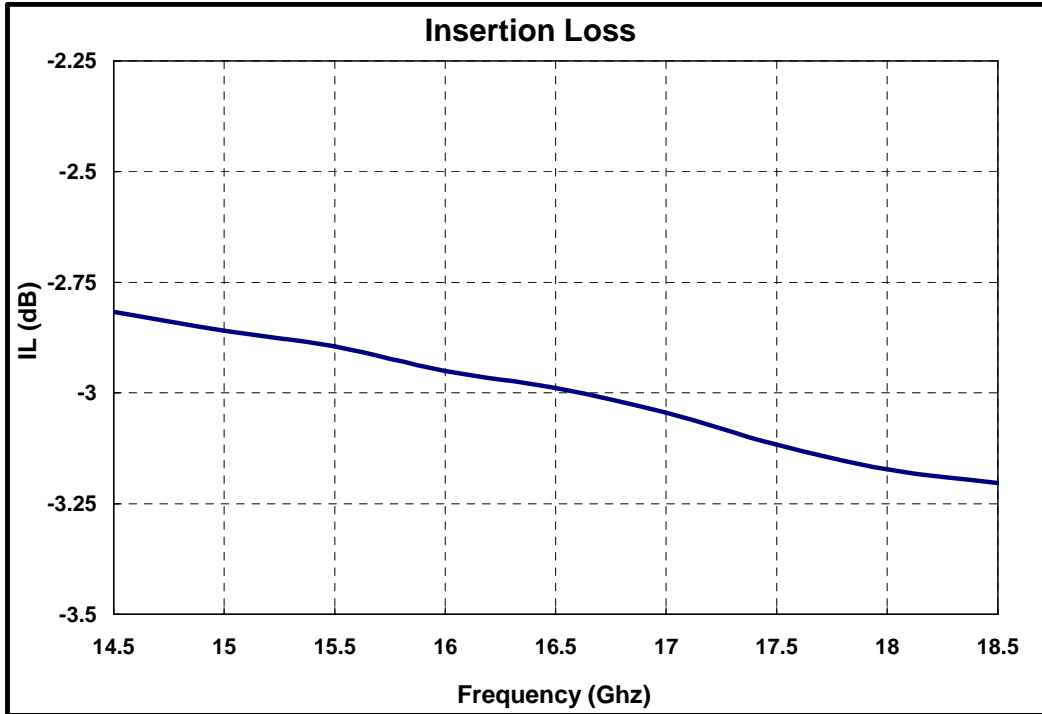
Parameter	Value	Units
Frequency Range	14.5 – 18.5	GHz
Insertion Loss	3.25	dB
Attenuation Range	0-31.5	dB
Attenuation step	0.5	dB
Attenuation Accuracy (All States)	2.5	dB
RMS Error	< 0.8	dB
Input/Output VSWR	1.4 : 1	
DC Supply	+5/6 , -5/3	V/mA
Control Voltage	0/+5	V

Note:

1. The above mentioned electrical specifications are measured On-Wafer.

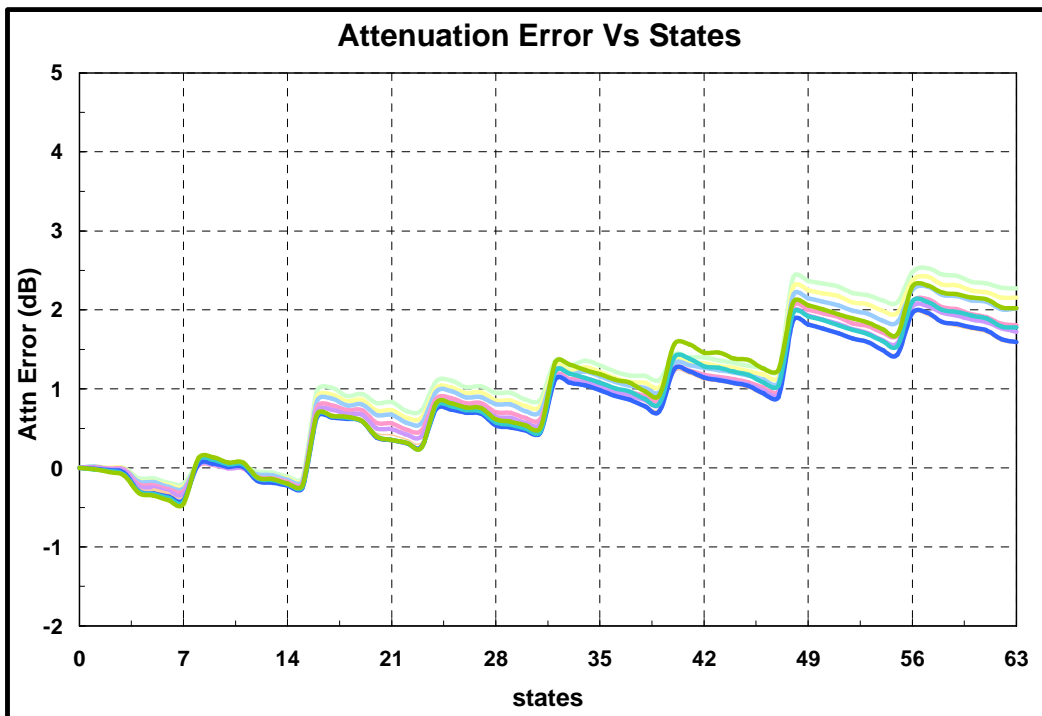
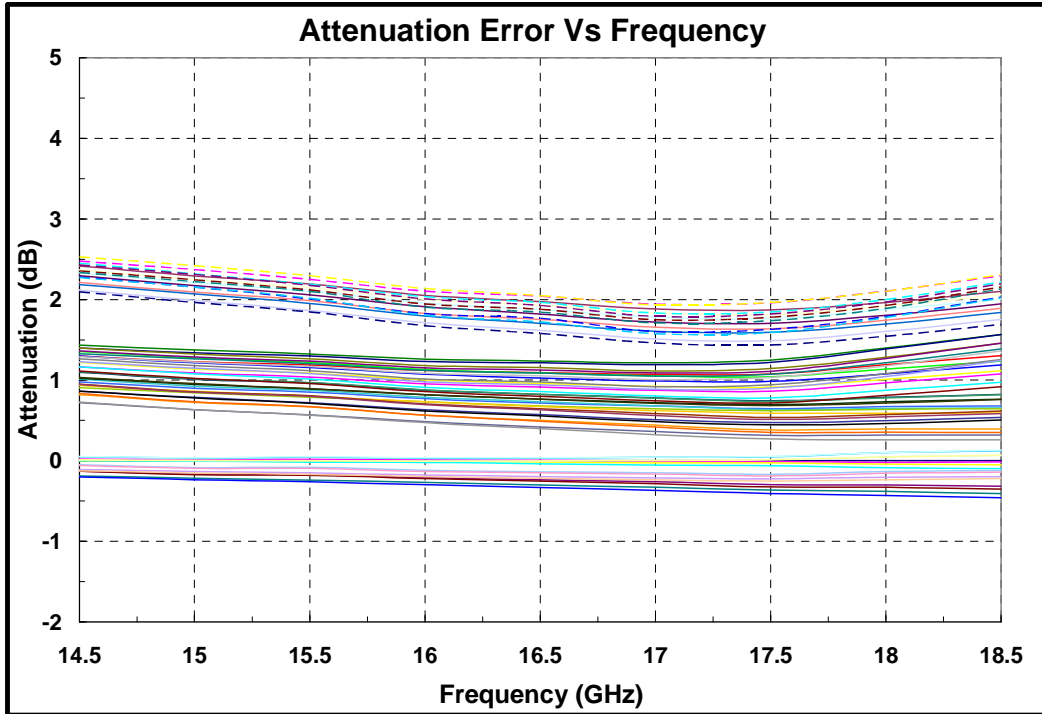
On Wafer data

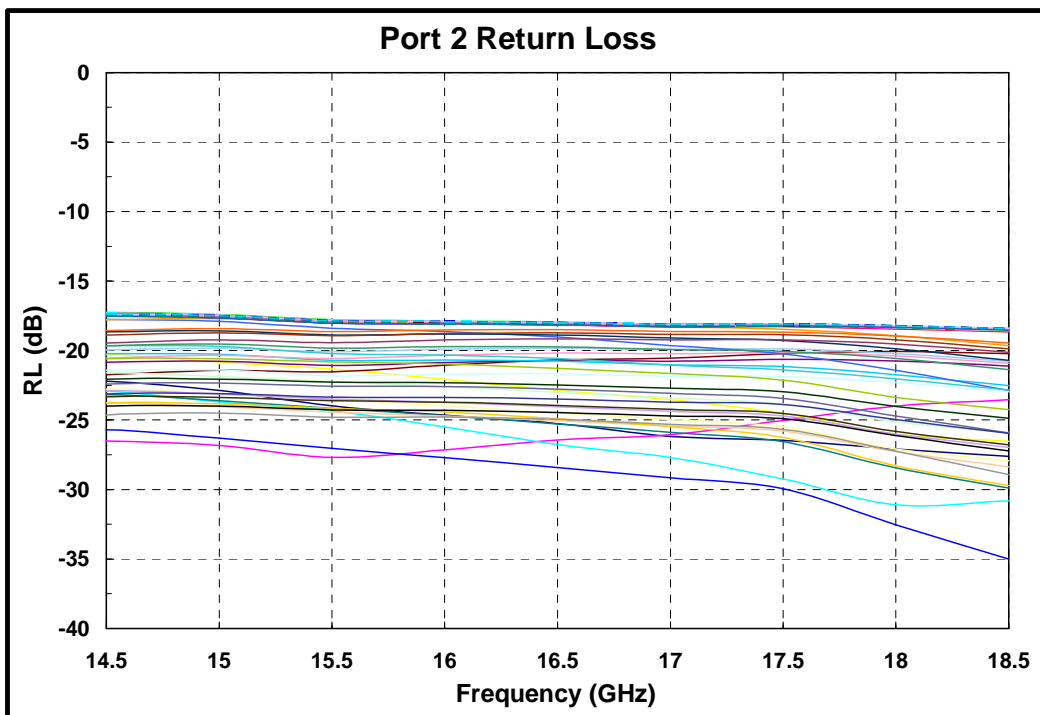
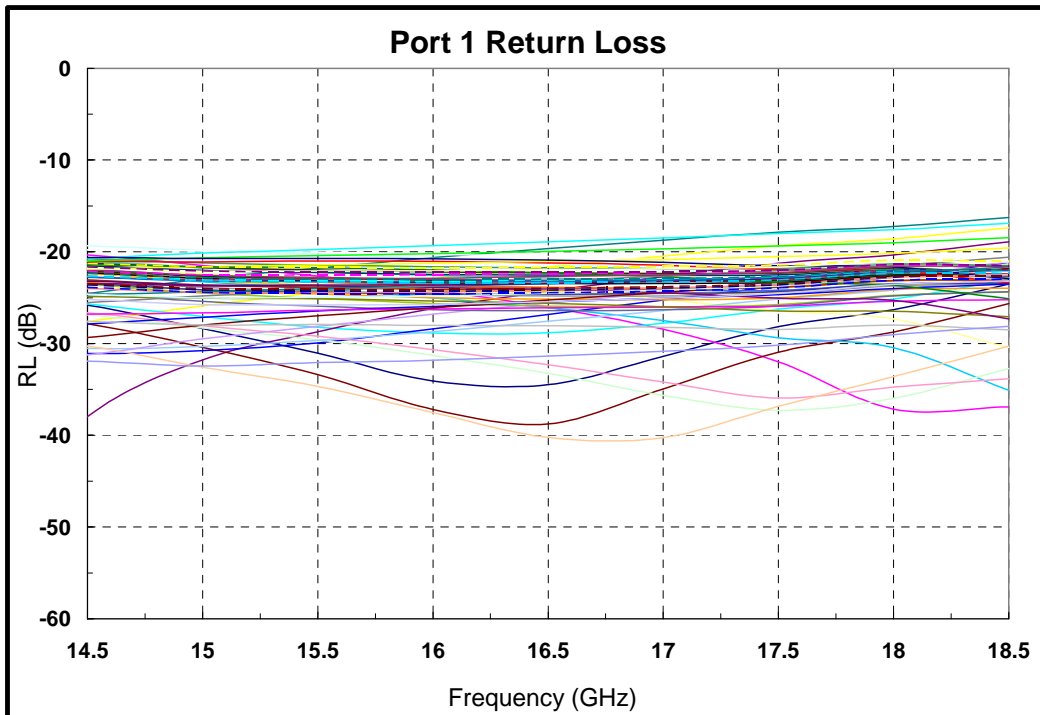
$T_A = 25^\circ\text{C}$

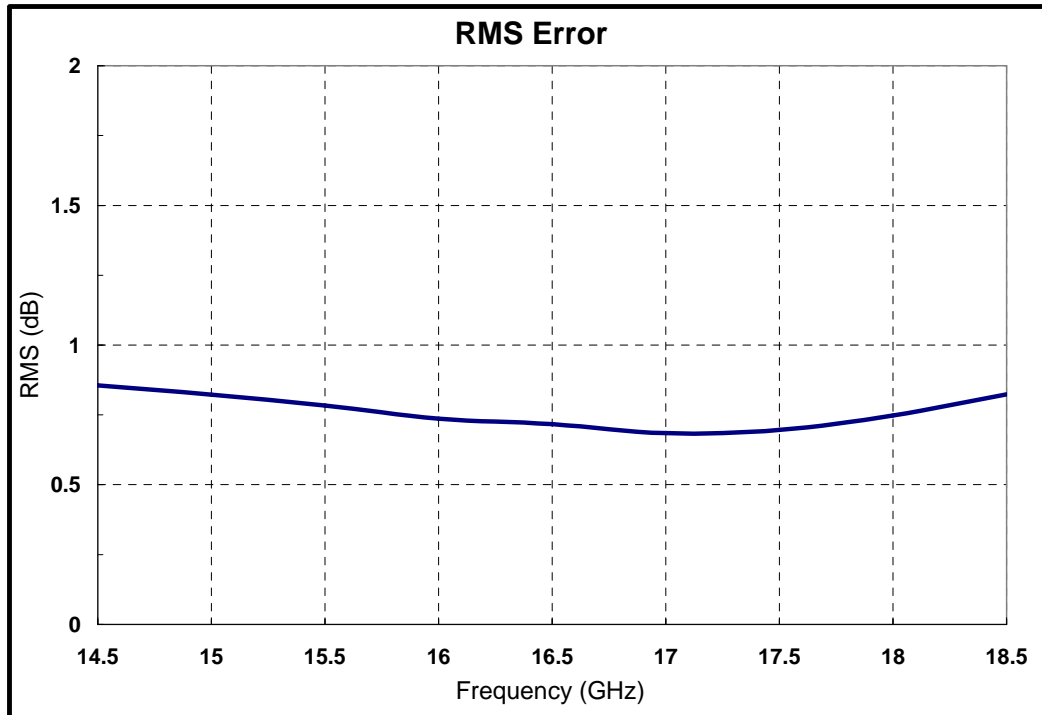


On Wafer data

$T_A = 25^\circ\text{C}$



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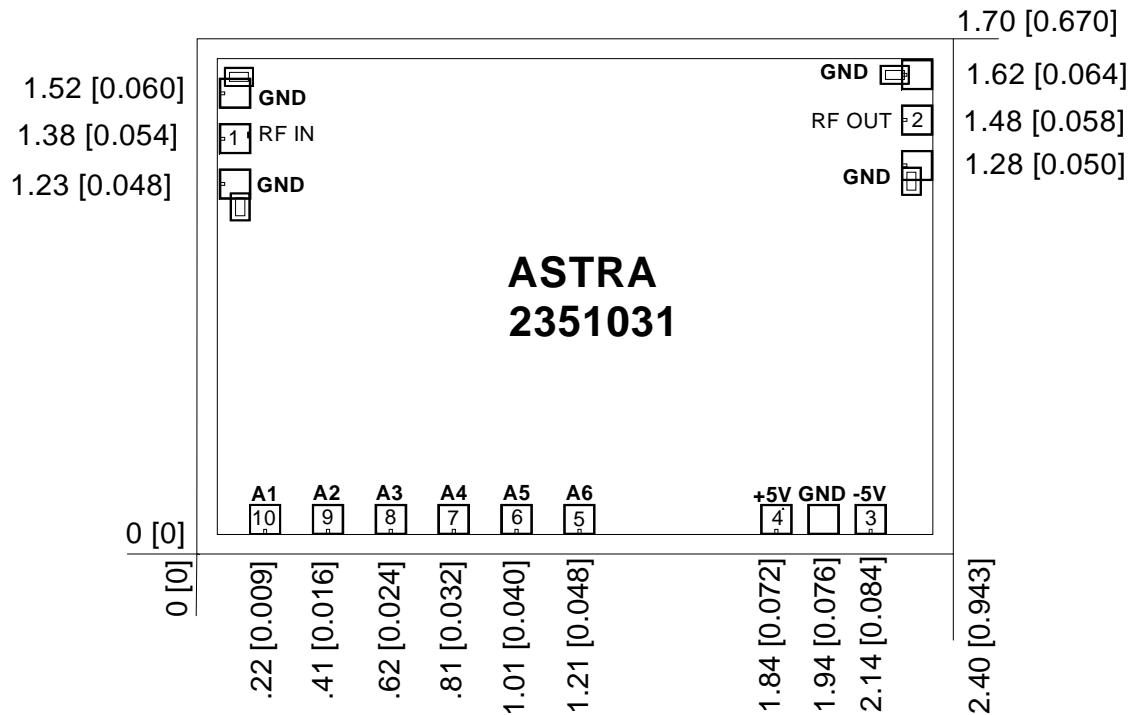
Truth Table

State	Attenuation (dB)	TTL Control (1 = 3.5 to 5 V, 0 = 0 to 0.5 V)					
		A6 (16)	A5 (8)	A4(4)	A3 (2)	A2(1)	A1 (0.5)
0	0	0	0	0	0	0	0
1	0.5	0	0	0	0	0	1
2	1	0	0	0	0	1	0
3	1.5	0	0	0	0	1	1
4	2	0	0	0	1	0	0
5	2.5	0	0	0	1	0	1
6	3	0	0	0	1	1	0
7	3.5	0	0	0	1	1	1
8	4	0	0	1	0	0	0
9	4.5	0	0	1	0	0	1
10	5	0	0	1	0	1	0
11	5.5	0	0	1	0	1	1
12	6	0	0	1	1	0	0
13	6.5	0	0	1	1	0	1
14	7	0	0	1	1	1	0
15	7.5	0	0	1	1	1	1
16	8	0	1	0	0	0	0
17	8.5	0	1	0	0	0	1
18	9	0	1	0	0	1	0
19	9.5	0	1	0	0	1	1
20	10	0	1	0	1	0	0
21	10.5	0	1	0	1	0	1
22	11	0	1	0	1	1	0
23	11.5	0	1	0	1	1	1
24	12	0	1	1	0	0	0
25	12.5	0	1	1	0	0	1
26	13	0	1	1	0	1	0
27	13.5	0	1	1	0	1	1
28	14	0	1	1	1	0	0
29	14.5	0	1	1	1	0	1
30	15	0	1	1	1	1	0
31	15.5	0	1	1	1	1	1
32	16	1	0	0	0	0	0
33	16.5	1	0	0	0	0	1
34	17	1	0	0	0	1	0
35	17.5	1	0	0	0	1	1

Truth Table

State	Attenuation (dB)	TTL Control (1 = 3.5 to 5 V, 0 = 0 to 0.5 V)					
		A6 (16)	A5 (8)	A4(4)	A3 (2)	A2(1)	A1 (0.5)
36	18.0	1	0	0	1	0	0
37	18.5	1	0	0	1	0	1
38	19	1	0	0	1	1	0
39	19.5	1	0	0	1	1	1
40	20	1	0	1	0	0	0
41	20.5	1	0	1	0	0	1
42	21	1	0	1	0	1	0
43	21.5	1	0	1	0	1	1
44	22	1	0	1	1	0	0
45	22.5	1	0	1	1	0	1
46	23	1	0	1	1	1	0
47	23.5	1	0	1	1	1	1
48	24	1	1	0	0	0	0
49	24.5	1	1	0	0	0	1
50	25	1	1	0	0	1	0
51	25.5	1	1	0	0	1	1
52	26	1	1	0	1	0	0
53	26.5	1	1	0	1	0	1
54	27	1	1	0	1	1	0
55	27.5	1	1	0	1	1	1
56	28	1	1	1	0	0	0
57	28.5	1	1	1	0	0	1
58	29	1	1	1	0	1	0
59	29.5	1	1	1	0	1	1
60	30	1	1	1	1	0	0
61	30.5	1	1	1	1	0	1
62	31	1	1	1	1	1	0
63	31.5	1	1	1	1	1	1

Mechanical Characteristics

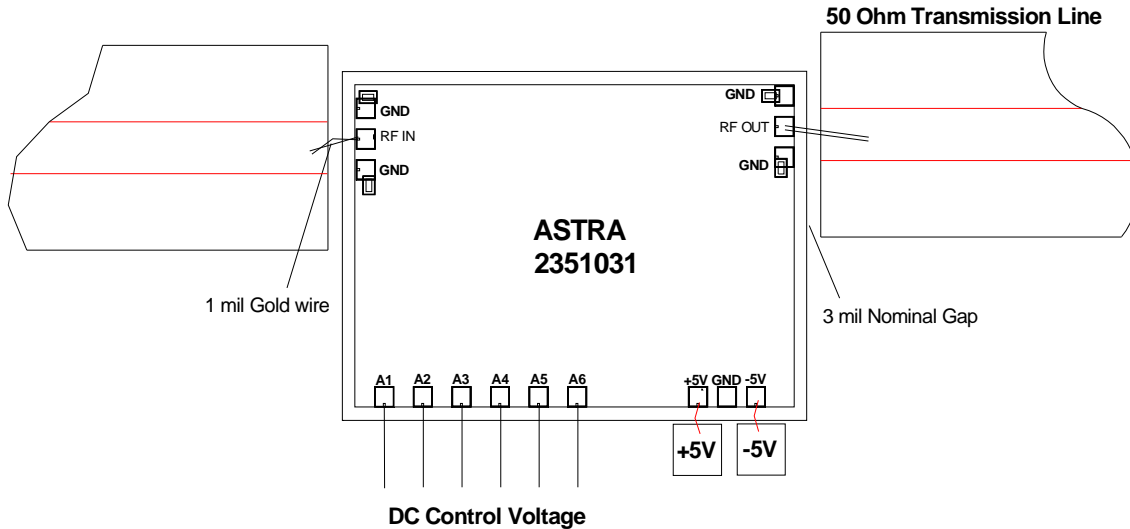


Units: millimeters (inches)

Note:

1. All RF and DC bond pads are 100µm x 100µm
2. Pad no.1: RF Port 1
3. Pad no.2: RF Port 2
4. Pad no.3: -5V
5. Pad no.4: +5V
6. Pad nos.5 -10: Control pads; Pad 5: MSB(16dB) & Pad 10: LSB (0.5dB)

Recommended Assembly Diagram


Note:

1. The RF input & output ports are DC coupled
2. No external components are required for this chip

Die attach: For Epoxy attachment, use of a two-component conductive epoxy is recommended. An epoxy fillet should be visible around the total die periphery. If Eutectic attachment is preferred, use of fluxless AuSn (80/20) 1-2 mil thick preform solder is recommended. Use of AuGe preform should be strictly avoided.

Wire bonding: For DC pad connections use either ball or wedge bonds. For best RF performance, use of 150 - 200 μ m length of wedge bonds is advised. Single Ball bonds of 250-300 μ m though acceptable, may cause a deviation in RF performance.



GaAs MMIC devices are susceptible to Electrostatic discharge. Proper precautions should be observed during handling, assembly & testing

All information and Specifications are subject to change without prior notice